EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7806	438/22,48-53.ccls. 257/254,419.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:23
L2	522	L1 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:23
L3	65	L2 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:23
L4	207298	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:24
L5	18690	L4 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:24
L6	4201	L5 and (trench via groove hole recess opening via cavity) near3 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:24
L7	304	L6 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:24

L8	52	L7 and (movable diaphragm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:24
L9	207298	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L10	18690	L9 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L11	5726	L10 and (trench via groove hole recess opening via cavity) near3 etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L12	601	L11 and (aperture acoutic near3 hole) with (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L13	932	silicon near3 microphone	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L14	454	L13 and diaphragm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25
L15	95	L14 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/07/29 09:25

S63	45	("0106828" | "20050187204" | "5408731")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:11
S64	2	("20050187204")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:11
S65	1	10/558885	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:12
S67	6	("0106828" | "20050187204" | "5408731").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:35
S68	2	("20050187204").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:36
S69	883	silicon near3 microphone	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:38
S70	434	S69 and diaphragm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:39
S71	90	S70 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:39

S72	200119	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:00
S73	40040	(first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:01
S74	18062	S72 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:01
S75	4075	S74 and (trench via groove hole recess opening via cavity) near3 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:02
S76	291	S75 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:05
S77	50	S76 and (movable diaphragm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:06
S78	200243	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59
S79	18064	S78 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59

S80	5508	S79 and (trench via groove hole recess opening via cavity) near3 etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59
S81	569	S80 and (aperture acoutic near3 hole) with (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:00
S82	5	S80 and (aperture acoutic near3 hole) with (aperture acoutic near3 hole) same (microphone pressure near3 sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:01
S83	5	S80 and (aperture acoutic near3 hole) same (microphone pressure near3 sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:04
S84	7536	438/22,48-53.ccls. 257/254,419.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:05
S85	1688	S84 and first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:06
S86	499	S84 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:07
S87	63	S86 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:07

S88	183	S86 and (trench via groove hole recess opening via cavity) near3 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:08

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